Kohei Hamaya

List of Publications by Year
in descending order

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216 papers	3,863 citations	109321 35 h-index	189892 50 g-index
219 all docs	219 docs citations	219 times ranked	1723 citing authors

#	Article	IF	Citations
1	Converse Magnetoelectric Effect in Epitaxial Coâ„MnSi/Pb(Mg_{1/3}Nb_{2/3})Oâ„-PbTiOâ„ Multiferroic Heterostructures. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	3
2	Temperature Dependence of Two-Terminal Local Magnetoresistance in Co-Based Heusler Alloy/Ge Lateral Spin-Valve Devices. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	1
3	Mechanism of crack formation in strained SiGe(1 1 1) layers. Journal of Crystal Growth, 2022, 589, 126672.	1.5	2
4	Significant effect of interfacial spin moments in ferromagnet-semiconductor heterojunctions on spin transport in a semiconductor. Physical Review B, 2022, 105, .	3.2	0
5	Giant converse magnetoelectric effect in a multiferroic heterostructure with polycrystalline Co2FeSi. NPG Asia Materials, 2022, 14, .	7.9	13
6	Structural insight using anomalous XRD into Mn2CoAl Heusler alloy films grown by magnetron sputtering, IBAS, and MBE techniques. Acta Materialia, 2022, 235, 118063.	7.9	2
7	Strong room-temperature EL emission from Ge-on-Si (111) diodes. Journal of Crystal Growth, 2022, , 126766.	1.5	2
8	Semiconductor spintronics with Co2-Heusler compounds. MRS Bulletin, 2022, 47, 584-592.	3.5	13
9	Epitaxial Mn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si86.svg" display="inline" id="d1e594"><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:math>VAl films with <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si85.svg" display="inline" id="d1e602"><mml:mrow><mml:mi>L</mml:mi><mml:msub><mml:mrow><mml:mn>2</mml:mn></mml:mrow><mml:mrow><mml:mn	2.3	0
10	structure for all-Heusler stacks. Journal of Magnetism and Magnetic Materials, 2022, , 169644. Half-metallic nature of the low-temperature grown Co2MnSi films on SrTiO3. Journal of Alloys and Compounds, 2021, 854, 155571.	5.5	8
11	Experimental estimation of the spin diffusion length in undoped p-Ge on Fe3Si using vertical spin-valve devices. Journal of Applied Physics, 2021, 129, 013901.	2.5	1
12	A drastic increase in critical thickness for strained SiGe by growth on mesa-patterned Ge-on-Si. Applied Physics Express, 2021, 14, 025502.	2.4	5
13	Positive linear magnetoresistance effect in disordered <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>L</mml:mi><mml:msub><mml:mn>2</mml:mn><mml:mn> -type <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>Mn</mml:mi></mml:mrow><mml:mn>2 epitaxial films. Physical Review B, 2021, 103, .	3.2	15
14	Giant magnetoelectric effect in an L21-ordered Co2FeSi/Pb(Mg1/3Nb2/3)O3-PbTiO3 multiferroic heterostructure. Applied Physics Letters, 2021, 118, .	3.3	9
15	Room-temperature two-terminal magnetoresistance ratio reaching 0.1% in semiconductor-based lateral devices with L21-ordered Co2MnSi. Applied Physics Letters, 2021, 118, .	3.3	16
16	Effect of Fe atomic layers at the ferromagnetâ€“semiconductor interface on temperature-dependent spin transport in semiconductors. Journal of Applied Physics, 2021, 129, .	2.5	5
17	Experimental extraction of donor-driven spin relaxation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type nondegenerate germanium. Physical Review B, 2021, 104, .	3.2	4
18	Electric field tunable anisotropic magnetoresistance effect in an epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>2</mml:mn></mml: mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> interfacial multiferroic system. Physical Review Materials, 2021, 5, .	2.4	10

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19	Substrate dependent reduction of Gilbert damping in annealed Heusler alloy thin films grown on group IV semiconductors. Applied Physics Letters, 2021, 119, .	3.3	3
20	Superimposed contributions to two-terminal and nonlocal spin signals in lateral spin-transport devices. Physical Review B, 2021, 104, .	3.2	3
21	Magnetoresistance ratio of more than 1% at room temperature in germanium vertical spin-valve devices with Co2FeSi. Applied Physics Letters, 2021, 119, .	3.3	8
22	Control of thermoelectric properties in Mn-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Mn</mml:mi><mml:mn>x</mml:mn></mml:r epilayers. Physical Review B, 2020, 102, .	3.2	5
23	Enhancement of the Spin Hall Angle by Interdiffusion of Atoms in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Co</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mrow><mml:mi>Fe</mml:mi> / n - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inl. Physical Review Applied, 2020, 14, .	3.8	5
24	Study of Spin Transport and Magnetoresistance Effect in Silicon-based Lateral Spin Devices for Spin-MOSFET Applications. Journal of the Magnetics Society of Japan, 2020, 44, 56-63.	0.9	1
25	Suppression of Donor-Driven Spin Relaxation in Strained <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Si</mml:mi><mml:mrow><mml:mn>0.1</mml:mn></mml:mrow></mml:msub><mml:msub> Physical Review Applied, 2020, 13, .	3.8	13
26	Crack formation in strained SiGe grown on Ge-on-Si (111) and its suppression by patterning substrates. Materials Science in Semiconductor Processing, 2020, 117, 105153.	4.0	8
27	Germanium pn junctions between ferromagnetic CoFe and Fe3Si layers for spintronic applications. Materials Science in Semiconductor Processing, 2020, 116, 105066.	4.0	3
28	Inverse local magnetoresistance effect up to room temperature in ferromagnet-semiconductor lateral spin-valve devices. Materials Science in Semiconductor Processing, 2020, 113, 105046.	4.0	2
29	Spin injection through energy-band symmetry matching with high spin polarization in atomically controlled ferromagnet/ferromagnet/semiconductor structures. NPG Asia Materials, 2020, 12, .	7.9	32
30	Thermoelectric properties of single-phase full-Heusler alloy Fe2TiSi films with D3-type disordering. Journal of Applied Physics, 2020, 127, .	2.5	12
31	Spin transport in antimony-doped germanium detected using vertical spin-valve structures. Applied Physics Express, 2020, 13, 023001.	2.4	4
32	Growth of ferromagnetic Co2FeSi films on flexible Ge(111). Materials Science in Semiconductor Processing, 2020, 112, 104997.	4.0	1
33	Proximity exchange coupling across an MgO tunnel barrier detected via spin precession. , 2020, , .		1
34	(Invited) Strain Engineering of Si/Ge Heterostructures on Ge-on-Si Platform. ECS Transactions, 2020, 98, 267-276.	0.5	1
35	Increased Critical Thickness for Strained SiGe on Ge-on-Si(111). ECS Transactions, 2020, 98, 499-503.	0.5	2
36	Nonmonotonic bias dependence of local spin accumulation signals in ferromagnet/semiconductor lateral spin-valve devices. Physical Review B, 2019, 100, .	3.2	14

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37	Critical thickness of strained Si_{1-x}Ge_x on Ge(111) and Ge-on-Si(111). Applied Physics Express, 2019, 12, 081005.	2.4	9
38	Great Differences between Low-Temperature Grown Co₂FeSi and Co₂MnSi Films on Single-Crystalline Oxides. ACS Applied Electronic Materials, 2019, 1, 2371-2379.	4.3	10
39	Hanle spin precession in a two-terminal lateral spin valve. Applied Physics Letters, 2019, 114, 242401.	3.3	10
40	Magnetic and Transport Properties of Co1+<italic>x</italic>FeV1â^'<italic>x</italic>Si Epitaxial Films Grown by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2019, 55, 1-4.	2.1	1
41	Quantification of Spin Drift in Devices with a Heavily Doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Si</mml:mi></mml:math> Channel. Physical Review Applied, 2019, 11, .	3.8	12
42	Room-temperature local magnetoresistance effect in n-Ge devices with low-resistive Schottky-tunnel contacts. Applied Physics Express, 2019, 12, 033002.	2.4	11
43	Significant reduction in the thermal conductivity of Si-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> epilayers. Physical Review B, 2019, 99, .	3.2	15
44	Experimental verification of the origin of positive linear magnetoresistance in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>CoFe</mml:mi><mml:mo>(</mml:mo><mml:msub><mml:mrow><mml:mn> Heusler alloys. Physical Review B, 2019, 100, .	3.2	9
45	Proximity exchange coupling in a Fe/MgO/Si tunnel contact detected by the inverted Hanle effect. Physical Review B, 2019, 100, .	3.2	5
46	Direct observation of pseudo-gap electronic structure in the Heusler-type Fe2VAl thin film. Journal of Electron Spectroscopy and Related Phenomena, 2019, 232, 1-4.	1.7	9
47	Crystal orientation effect on spin injection/detection efficiency in Si lateral spin-valve devices. Journal Physics D: Applied Physics, 2019, 52, 085102.	2.8	1
48	Anomalous Hall conductivity and electronic structures of Si-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Mn</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> epitaxial films. Physical Review B, 2018, 97, .	3.2	21
49	Effect of Feâ€“V nonstoichiometry on electrical and thermoelectric properties of Fe₂VAl films. Japanese Journal of Applied Physics, 2018, 57, 040306.	1.5	9
50	Magnetic and structural depth profiles of Heusler alloy Co₂FeAl_{0.5}Si_{0.5} epitaxial films on Si(1â€‰1â€‰1). Journal of Physics Condensed Matter, 2018, 30, 065801.	1.8	3
51	Effect of annealing on the structure and magnetic properties of Co2FeAl0.5Si0.5 thin films on Ge(111). Journal of Alloys and Compounds, 2018, 748, 323-327.	5.5	10
52	Pure spin current transport in a SiGe alloy. Applied Physics Express, 2018, 11, 053006.	2.4	18
53	Large local magnetoresistance at room temperature in Si<100> devices. , 2018, , .		0
54	Nonlinear Electrical Spin Conversion in a Biased Ferromagnetic Tunnel Contact. Physical Review Applied, 2018, 10, .	3.8	21

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55	Epitaxial growth of Sb-doped Ge layers on ferromagnetic Fe₃Si for vertical semiconductor spintronic devices. Semiconductor Science and Technology, 2018, 33, 104008.	2.0	5
56	Observation of local magnetoresistance signals in a SiGe-based lateral spin-valve device. Semiconductor Science and Technology, 2018, 33, 114009.	2.0	12
57	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	3.2	15
58	Spin transport and relaxation in germanium. Journal Physics D: Applied Physics, 2018, 51, 393001.	2.8	48
59	Spin Absorption Effect at Ferromagnet/Ge Schottky-Tunnel Contacts. Materials, 2018, 11, 150.	2.9	1
60	Modulation of magnetization dynamics in an epitaxial Heusler ferromagnet due to pure spin current in a laterally configured structure. Journal of Physics Condensed Matter, 2018, 30, 255802.	1.8	1
61	Local Magnetoresistance at Room Temperature in Si <inline-formula> <tex-math notation="LaTeX">$langle100angle$ </tex-math> </inline-formula> Devices. IEEE Transactions on Magnetics, 2018, 54, 1-4.	2.1	11
62	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250â€‰Â°C. Journal of Applied Physics, 2018, 123, 215704.	2.5	24
63	Magnetic and transport properties of equiatomic quaternary Heusler CoFeVSi epitaxial films. Physical Review Materials, 2018, 2, .	2.4	17
64	Electrical properties of epitaxial Lu- or Y-doped La 2 O 3 /La 2 O 3 /Ge high- k gate-stacks. Materials Science in Semiconductor Processing, 2017, 70, 260-264.	4.0	8
65	Low-temperature growth of fully epitaxial CoFe/Ge/Fe₃Si layers on Si for vertical-type semiconductor spintronic devices. Semiconductor Science and Technology, 2017, 32, 094005.	2.0	17
66	Spin relaxation through lateral spin transport in heavily doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type silicon. Physical Review B, 2017, 95, .	3.2	38
67	Robust spin-current injection in lateral spin valves with two-terminal Co2FeSi spin injectors. AIP Advances, 2017, 7, 055808.	1.3	2
68	Room-temperature spin transport in n-Ge probed by four-terminal nonlocal measurements. Applied Physics Express, 2017, 10, 093001.	2.4	31
69	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	3.3	20
70	Low thermal conductivity of thermoelectric Fe₂VAl films. Applied Physics Express, 2017, 10, 115802.	2.4	12
71	Spin Transport and Relaxation up to 250 K in Heavily Doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>n</mml:mi></mml:math> -Type Ge Detected Using <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Co</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></ Physical Review Applied, 2017, 8, .	3.8	52
72	Large impact of impurity concentration on spin transport in degenerate n -Ge. Physical Review B, 2017, 95, .	3.2	22

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73	Influence of the Ge diffusion on the magnetic and structural properties in Fe3Si and CoFe epilayers grown on Ge. Journal of Crystal Growth, 2017, 468, 676-679.	1.5	9
74	Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous Î´-doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85.	4.0	12
75	Effect of post annealing on hole mobility of pseudo-single-crystalline germanium films on glass substrates. Materials Science in Semiconductor Processing, 2017, 70, 68-72.	4.0	5
76	Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, .	3.8	47
77	Atomic study of Hybrid Spintronic Heterostructures: Co2FeAl05Si0.5/Ge(111). Microscopy and Microanalysis, 2017, 23, 1762-1763.	0.4	0
78	Electrical detection of spin accumulation and relaxation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math> -type germanium. Physical Review Materials, 2017, 1, .	2.4	16
79	Spin signals in Si non-local transport devices with giant spin accumulation. , 2017, , .		1
80	Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766.	1.2	14
81	Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, .	1.3	4
82	Atomic and electronic structure study of a Co 2 FeAl 0.5 Si 0.5 half-metal thin film on Si(111). Microscopy and Microanalysis, 2016, 22, 1524-1525.	0.4	0
83	Spin transport in p-Ge through a vertically stacked Ge/Fe3Si junction. Applied Physics Letters, 2016, 109, .	3.3	23
84	Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co2FeSi0.5Al0.5/Ge(111). Scientific Reports, 2016, 6, 37282.	3.3	18
85	All-epitaxial Co2FeSi/Ge/Co2FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, .	2.5	17
86	Temperature-independent spin relaxation in heavily doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type germanium. Physical Review B, 2016, 94, .	3.2	30
87	The role of chemical structure on the magnetic and electronic properties of Co2FeAl0.5Si0.5/Si(111) interface. Applied Physics Letters, 2016, 108, .	3.3	15
88	The antiphase boundary in half-metallic Heusler alloy Co2Fe(Al,Si): atomic structure, spin polarization reversal, and domain wall effects. Applied Physics Letters, 2016, 109, .	3.3	9
89	Controlling the half-metallicity of Heusler/Si(1â€‰1â€‰1) interfaces by a monolayer of Siâ€“Coâ€“Si. Journal of Physics Condensed Matter, 2016, 28, 395003.	1.8	3
90	Spin injection into multilayer graphene from highly spin-polarized Co2FeSi Heusler alloy. Applied Physics Express, 2016, 9, 063006.	2.4	15

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91	(Invited) Finely Controlled Heterointerfaces between Ge(111) and Metallic Alloys or Insulators for Next Generation Ge-Based Devices. ECS Transactions, 2016, 75, 651-659.	0.5	0
92	Magnetic properties and interfacial characteristics of all-epitaxial Heusler-compound stacking structures. Physical Review B, 2016, 94, .	3.2	4
93	Direct evidence for suppression of the Kondo effect due to pure spin current. Physical Review B, 2016, 94, .	3.2	17
94	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001.	1.5	3
95	Structural and electrical properties of Ge(111) films grown on Si(111) substrates and application to Ge(111)-on-Insulator. Thin Solid Films, 2016, 613, 24-28.	1.8	36
96	MÃ¶ssbauer Analysis. Springer Series in Materials Science, 2016, , 341-352.	0.6	1
97	Low-temperature<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>B</mml:mi><mml:mn>2</mml:mn></mml:mrow></mml:math> and magnetic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>100</mml:mn></mml:mrow></mml:math> on bcc alloys. Physical Review B, 2015, 92, .	3.2	8
98	Electrical properties of pseudo-single-crystalline germanium thin-film-transistors fabricated on glass substrates. Applied Physics Letters, 2015, 107, .	3.3	44
99	Effect of atomic-arrangement matching on La2O3/Ge heterostructures for epitaxial high-k-gate-stacks. Journal of Applied Physics, 2015, 118, .	2.5	6
100	A pseudo-single-crystalline germanium film for flexible electronics. Applied Physics Letters, 2015, 106, .	3.3	44
101	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co₂FeSi electrodes. Applied Physics Express, 2015, 8, 043003.	2.4	12
102	Correlation between amplitude of spin accumulation signals investigated by Hanle effect measurement and effective junction barrier height in CoFe/MgO/n+-Si junctions. Journal of Applied Physics, 2015, 117, .	2.5	11
103	Spin transport and accumulation in n+-Si using Heusler compound Co2FeSi/MgO tunnel contacts. Applied Physics Letters, 2015, 107, .	3.3	21
104	High carrier mobility in orientation-controlled large-grain (â‰¥50â€‰Î¼m) Ge directly formed on flexible plastic by nucleation-controlled gold-induced-crystallization. Applied Physics Letters, 2014, 104, .	3.3	66
105	Reliable reduction of Fermi-level pinning at atomically matched metal/Ge interfaces by sulfur treatment. Applied Physics Letters, 2014, 104, 172109.	3.3	13
106	Improvement of magnetic and structural stabilities in high-quality Co2FeSi1â^'xAlx/Si heterointerfaces. Applied Physics Letters, 2014, 105, .	3.3	34
107	Effect of Sn-doped Ge insertion layers on epitaxial growth of ferromagnetic Fe<inf>3</inf>Si films on a flexible substrate. , 2014, , .		0
108	Large anisotropy of Gilbert damping constant in L2₁-ordered Co₂FeSi film. Applied Physics Express, 2014, 7, 123001.	2.4	18

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109	An All-Epitaxial Fe₃Si/FeSi/Co₂FeSi Trilayer Grown by Room-Temperature Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2014, 50, 1-3.	2.1	4
110	Local magnetoresistance through Si and its bias voltage dependence in ferromagnet/MgO/silicon-on-insulator lateral spin valves. Journal of Applied Physics, 2014, 115, .	2.5	27
111	Formation of Ge(111) on Insulator by Ge epitaxy on Si(111) and layer transfer. Thin Solid Films, 2014, 557, 76-79.	1.8	10
112	A magnetic tunnel junction with an L21-ordered Co2FeSi electrode formed by all room-temperature fabrication processes. Thin Solid Films, 2014, 557, 386-389.	1.8	7
113	Low-temperature Grown Ge<inf>1−x</inf>Sn<inf>x</inf> layers on a metallic silicide. , 2014, , .		0
114	Atomically controlled heteroepitaxy of Ge on a ferromagnetic heusler alloy for a vertical-type spin transistor. , 2014, , .		0
115	Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound Co₂FeSi electrodes. Applied Physics Express, 2014, 7, 033002.	2.4	65
116	Room-temperature electrical creation of spin accumulation in n-Ge using highly resistive Fe3Si/n+-Ge Schottky-tunnel contacts. Thin Solid Films, 2014, 557, 382-385.	1.8	6
117	High-quality Co2FeSi0.5Al0.5/Si heterostructures for spin injection in silicon spintronic devices. Thin Solid Films, 2014, 557, 390-393.	1.8	18
118	Giant enhancement of spin pumping efficiency using Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>Si ferromagnet. Physical Review B, 2013, 88, .	3.2	33
119	Maximum magnitude in bias-dependent spin accumulation signals of CoFe/MgO/Si on insulator devices. Journal of Applied Physics, 2013, 114, .	2.5	21
120	Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth Fe3Si/Si(111) contact. Journal of Applied Physics, 2013, 113, .	2.5	14
121	Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metalâ€“oxideâ€“semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, .	2.5	20
122	Effect of Co-Fe substitution on room-temperature spin polarization in Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Si Heusler-compound films. Physical Review B, 2013, 88, .	3.2	14
123	Generation and Detection of a Pure Spin Current Using Co-Based Heusler-Alloy Spin Injector and Detector: Comparison of Co2MnSi and Co2FeSi. ECS Transactions, 2013, 50, 245-251.	0.5	1
124	Dynamical Spin Injection into p-Type Germanium at Room Temperature. Applied Physics Express, 2013, 6, 023001.	2.4	39
125	(Invited) SiGe Spintronics with Single-Crystalline Ferromagnetic Schottky-Tunnel Contacts. ECS Transactions, 2013, 50, 235-243.	0.5	0
126	Effect of an Atomically Matched Structure on Fermi-level Pinning at Metal/p-Ge Interfaces. ECS Transactions, 2013, 50, 223-229.	0.5	4

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127	Lateral spin valves with two-different Heusler-alloy electrodes on the same platform. Applied Physics Letters, 2013, 103, .	3.3	14
128	Qualitative study of temperature-dependent spin signals in n-Ge-based lateral devices with Fe3Si/n+-Ge Schottky-tunnel contacts. Journal of Applied Physics, 2013, 113, .	2.5	34
129	An ultra-thin buffer layer for Ge epitaxial layers on Si. Applied Physics Letters, 2013, 102, .	3.3	22
130	Ion beam analysis of quaternary Heusler alloy Co₂(Mn_{1â€“x}Fe_x)Si(111) epitaxially grown on Ge(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1828-1831.	0.8	0
131	Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a D0₃-Fe₃Si Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02.	1.5	10
132	Molecular Beam Epitaxy of Co₂MnSi Films on Group-IV Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 04CM06.	1.5	14
133	Temperature evolution of spin accumulation detected electrically in a nondegenerated silicon channel. Physical Review B, 2012, 85, .	3.2	31
134	Estimation of the spin polarization for Heusler-compound thin films by means of nonlocal spin-valve measurements: Comparison of Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>FeSi and Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>Si. Physical Review B, 2012, 85, .	3.2	81
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